

< X/Ku band internally matched power GaAs FET >

MGFK39V4045

14.0 - 14.5 GHz BAND / 8W

DESCRIPTION

The MGFK39V4045 is an internally impedance-matched GaAs power FET especially designed for use in 14.0 – 14.5 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Internally matched to 50(ohm) system

- Flip-chip mounted
 High output power
 - P̃1dB=8W (TYP.) @f=14.0 − 14.5GHz
- High linear power gain
 - GLP=5.5dB (TYP.) @f=14.0 14.5GHz
- High power added efficiency
 - P.A.E.=20% (TYP.) @f=14.0 14.5GHz

APPLICATION

• 14.0 - 14.5 GHz band power amplifiers

QUALITY GRADE

• IG

www.BDTIC.com

RECOMMENDED BIAS CONDITIONS

• VDS=10V • ID=2.4A Refer to Bias Procedure

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain breakdown voltage	-15	V
VGSO	Gate to source breakdown voltage	-15	V
ID	Drain current	6	Α
IGR	Reverse gate current	-18	mA
IGF	Forward gate current	36	mA
PT *1	Total power dissipation	42.8	W
Tch	Cannel temperature	175	°C
Tstg	Storage temperature	-65 to +175	°C

*1: Tc=25°C

OUTLINE DRAWING Unit: millimeters (inches) 21.0 ± 0.3 (0.827 ± 0.012) (0.079MI 0.6 ± 0.15 (0.024 ± 0.006) 12.9±0.2 (0.508±0.008) (0.445) R1.6 (R0.063) (0.079 MIN) 3 10.7 (0.421) 17.0 ± 0.2 (0.102 ± 0.008) (0.669 ± 0.008) 0.1(0.004)1.6 (0.063) 4.5±0.4 177±0.016) 9 12.0 (0.472) (T) GATE 2 SOURCE (FLANGE) GF-8 (3) DRAIN

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Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits		Unit	
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	4	6	Α
gm	Transconductance	VDS=3V,ID=2.4A	1.2	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=20mA	-2	-	-5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=2.4A	38.5	39	-	dBm
GLP	Linear Power Gain	f=14.0 – 14.5GHz	4.5	5.5	-	dB
PAE	Power added efficiency		-	20	-	%
Rth(ch-c) *2	Thermal resistance	delta Vf method	-	-	3.5	°C/W

*2 : Channel-case

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